SPECIFICATION OF LED CHIP
C1550-30
[NIR]

1) Commodity Type and Physical Characteristics.

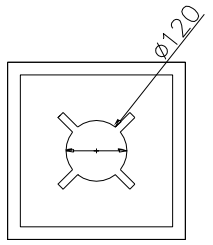
1. Material		InGaAsP/InP(DDH)	
2. Electrode	Top Side	P (anode) side	: Au Alloy
	Bottom Side	N (cathode) side	: Au Alloy
3. Electrode Pattern			Fig.1
4. Chip Size			Fig.2
5. Chip Thickness			Fig.2
6. Emission Area			Fig.2

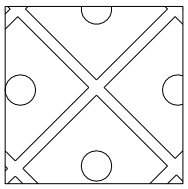
2) Electro-Optical Characteristics [Ta=25°C]

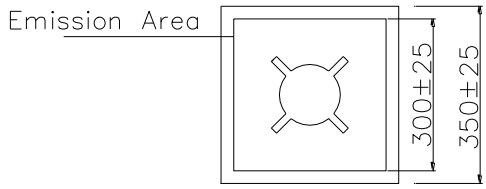
parameters	symbol	condition	min.	typ.	max.	unit
Forward Voltage	Vf	If=20mA		0.9	1.3	V
		If=50mA		1.0	1.4	
Reverse Current	Ir	Vr=3V			10	uA
Power Intensity	Po	If=20mA		0.6		mW
		If=50mA		1.2		
Peak Wavelength	λP	If=20mA	1500	1550	1600	nm
Spectral Radiation Bandwidth	Δλ	If=20mA		100		nm
RiseTime	tr	If=20mA		25		ns
FallTime	tf	If=20mA		20		ns

‡ Die shall be mounted on TO=18 gold header without resin coated.
‡ Power intensity is measured by PD G8370-85.

[Unit: um]







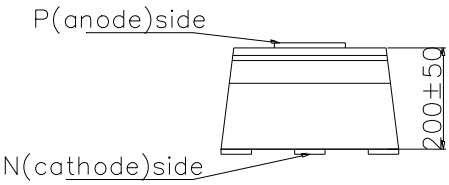


Fig.1 Electrode Pattern

Fig.2 Chip size and Emission Area

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